

# 2SB1612

2SB1612 代理商

## Silicon PNP epitaxial planer type

For low-frequency amplification  
Complementary to 2SD2474

### Features

- Low collector to emitter saturation voltage  $V_{CE(sat)}$
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

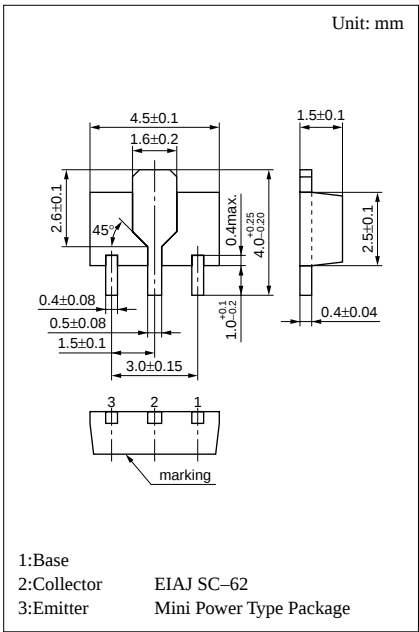
### Absolute Maximum Ratings (Ta=25°C)

| Parameter                    | Symbol    | Ratings    | Unit |
|------------------------------|-----------|------------|------|
| Collector to base voltage    | $V_{CBO}$ | -10        | V    |
| Collector to emitter voltage | $V_{CEO}$ | -10        | V    |
| Emitter to base voltage      | $V_{EBO}$ | -7         | V    |
| Peak collector current       | $I_{CP}$  | -2.4       | A    |
| Collector current            | $I_C$     | -2         | A    |
| Collector power dissipation  | $P_C^*$   | 1          | W    |
| Junction temperature         | $T_j$     | 150        | °C   |
| Storage temperature          | $T_{stg}$ | -55 ~ +150 | °C   |

\* Printed circuit board: Copper foil area of 1cm<sup>2</sup> or more, and the board thickness of 1.7mm for the collector portion

### Electrical Characteristics (Ta=25°C)

| Parameter                               | Symbol        | Conditions                             | min | typ   | max   | Unit |
|-----------------------------------------|---------------|----------------------------------------|-----|-------|-------|------|
| Collector cutoff current                | $I_{CBO}$     | $V_{CB} = -7V, I_E = 0$                |     |       | -1    | μA   |
| Collector to base voltage               | $V_{CBO}$     | $I_C = -10\mu A, I_E = 0$              | -10 |       |       | V    |
| Collector to emitter voltage            | $V_{CEO}$     | $I_C = -1mA, I_B = 0$                  | -10 |       |       | V    |
| Emitter to base voltage                 | $V_{EBO}$     | $I_E = -10\mu A, I_C = 0$              | -7  |       |       | V    |
| Forward current transfer ratio          | $h_{FE}$      | $V_{CE} = -2V, I_C = 200mA$            | 200 |       | 800   |      |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | $I_C = -1A, I_B = -10mA$               |     | -0.19 | -0.25 | V    |
| Transition frequency                    | $f_T$         | $V_{CB} = -6V, I_E = 50mA, f = 200MHz$ |     | 60    |       | MHz  |
| Collector output capacitance            | $C_{ob}$      | $V_{CB} = -6V, I_E = 0, f = 1MHz$      |     | 100   |       | pF   |



Marking symbol : 2F

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